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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Jiunn-Ren Hwang Examiner: Ruggles, John S
5 Anseime Chen
I-Hsiung Huang
Filing Date: 05/10/2001 Art Unit: 1756
Serial No.: 09/851,580 Docket No.: NAUP0292USA

10 Title: METHOD OF FORMING STORAGE NODES IN A DRAM

To: The Commissioner of Patents and Trademarks
Washington, D.C. 20231

15 Subject: Reply to the Office Action dated 12/18/2002

Dear Sir:

AMENDMENT

20 In response to the Office Action noted above, please
amend the above-identified application as follows:

In the Abstract:

On page 1, please replace the whole paragraph beginning
on line 4 as following:

25 A dynamic random access memory (DRAM) is formed on a
semiconductor wafer including a substrate, a thin film layer
positioned on the substrate, and a photoresist layer positioned
on the thin film layer. A first exposure process is performed
to form first exposure regions including a plurality of lines
30 parallel to each other and covering each storage node. A second
exposure process is performed to form second exposure regions
cutting the plurality of lines of the first exposure regions.